双路双输入正或门

查询样品: SN74LVC2G32-Q1

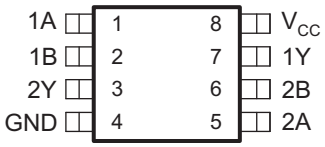
特性

- 符合汽车应用要求
- 具有符合 **AEC-Q100** 的下列结果：
  - 器件温度 **1** 级：**-40°C** 至 **125°C** 的环境运行温度范围
  - 器件人体模型 **(HBM)** 静电放电 **(ESD)** 分类等级 **H2**
  - 器件充电器件模型 **(CDM) ESD** 分类等级 **C3B**
- 输入接受的电压达到 **5.5V**
- **3.3V** 时，最大传播（延迟）时间为 **3.8ns**
- 低功耗，最大电源电流 **10μA**
- **3.3V** 时，输出驱动 **±24mA**
- 在V_{CC}**=3.3 V**，T_A**=25°C** 时，典型电压输出低峰值（输出地弹反射）
  <0.8V
- 在 V_{CC}**=3.3V**，T_A**=25°C** 时，典型电压输出高谷值 **(**V_{OH}下冲**)**
  >2V
- $I_{关闭}$状态电流支持部分断电模式运行

应用范围

- 车载应用
- 逻辑和栅极

DCU PACKAGE
(TOP VIEW)



说明

这个双路上输入正或门被设计用于 1.65V 至 5.5V 集流器电源电压运行。

SN74LVC2G32-Q1 在正逻辑中$Y = A + B$ or $Y = \overline{A} \bullet \overline{B}$执行布尔函数 。

NanoFree™ 封装技术是IC 封装概念的一项重大突破，它将硅晶片用作封装。

该器件完全符合使用关闭状态电流的部分断电应用的规范要求。 关闭状态电流电路禁用输出，从而可防止其断电时破坏性电流从该器件回流。

ORDERING INFORMATION(1)

T_A	PACKAGE(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 125°C	VSSOP - DCU	Reel of 3000	SN74LVC2G32QDCURQ1	SUCQ

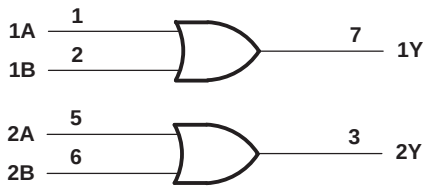
(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

FUNCTION TABLE (EACH GATE)

INPUTS		OUTPUT Y
A	B	
H	X	H
X	H	H
L	L	L

LOGIC DIAGRAM (POSITIVE LOGIC)



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	6.5	V
V_I	Input voltage range(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	6.5	V
V_O	Voltage range applied to any output in the high or low state(2) (3)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < 0		–50	mA
I_{OK}	Output clamp current	V_O < 0		–50	mA
I_O	Continuous output current			±50	mA
	Continuous current through V_{CC} or GND			±100	mA
T_{stg}	Storage temperature range		–65	150	°C
	ESD Rating	Human body model (HBM) AEC-Q100 classification level H2		2	kV
		Charged device model (CDM) AEC-Q100 classification level C3B		750	V

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(3) The value of V_{CC} is provided in the recommended operating conditions table.

THERMAL INFORMATION

THERMAL METRIC(1)		SN74LVC2G32-Q1 DCU (8 PINS)	UNIT
θ_{JA}	Junction-to-ambient thermal resistance	204.4	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance	77	
θ_{JB}	Junction-to-board thermal resistance	83.2	
ψ_{JT}	Junction-to-top characterization parameter	7.1	
ψ_{JB}	Junction-to-board characterization parameter	82.7	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	N/A	

(1) 有关传统和新的热 度量的更多信息，请参阅*IC 封装热度量*应用报告， SPRA953。

RECOMMENDED OPERATING CONDITIONS(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	5.5	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 3 V to 3.6 V	2		
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 3 V to 3.6 V		0.8	
		V_{CC} = 4.5 V to 5.5 V		0.3 × V_{CC}	
V_I	Input voltage		0	5.5	V
V_O	Output voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 3 V		–16	
				–24	
		V_{CC} = 4.5 V		–32	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 3 V		16	
				24	
		V_{CC} = 4.5 V		32	
Δt/Δv	Input transition rise or fall rate	V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20	ns/V
		V_{CC} = 3.3 V ± 0.3 V		10	
		V_{CC} = 5 V ± 0.5 V		5	
T_A	Operating free-air temperature		–40	125	°C

(1) All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	V_{CC}	MIN	TYP(1)	MAX	UNIT
V_{OH}		I_{OH} = –100 µA	1.65 V to 5.5 V	V_{CC} – 0.1			V
		I_{OH} = –4 mA	1.65 V	1.2			
		I_{OH} = –8 mA	2.3 V	1.9			
		I_{OH} = –16 mA	3 V	2.4			
		I_{OH} = –24 mA		2.3			
		I_{OH} = –32 mA	4.5 V	3.8			
V_{OL}		I_{OL} = 100 µA	1.65 V to 5.5 V			0.1	V
		I_{OL} = 4 mA	1.65 V			0.45	
		I_{OL} = 8 mA	2.3 V			0.3	
		I_{OL} = 16 mA	3 V			0.4	
		I_{OL} = 24 mA				0.6	
		I_{OL} = 32 mA	4.5 V			0.6	
I_I	A or B inputs	V_I = 5.5 V or GND	0 to 5.5 V			±5	µA
I_{off}		V_I or V_O = 5.5 V	0			±10	µA
I_{CC}		V_I = 5.5 V or GND, I_O = 0	1.65 V to 5.5 V			10	µA
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V			500	µA
C_i		V_I = V_{CC} or GND	3.3 V		5		pF

(1) All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

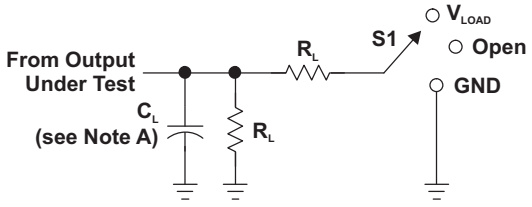
PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 3.3 V ± 0.3 V		V_{CC} = 5 V ± 0.5 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t_{pd}	A or B	Y	2.4	11	1	7.5	1	5.8	1	4.7	ns

OPERATING CHARACTERISTICS

T_A = 25°C

PARAMETER		TEST CONDITIONS	V_{CC} = 1.8 V	V_{CC} = 2.5 V	V_{CC} = 3.3 V	V_{CC} = 5 V	UNIT
			TYP	TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance	f = 10 MHz	17	17	17	19	pF

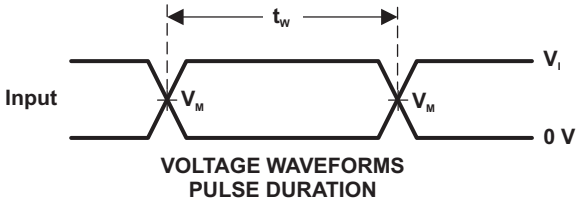
PARAMETER MEASUREMENT INFORMATION



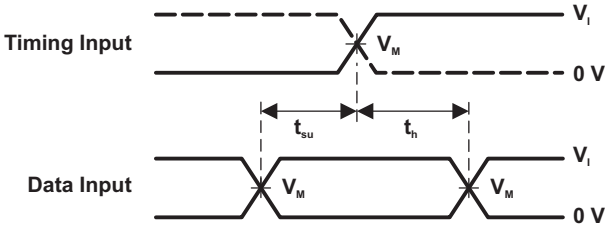
LOAD CIRCUIT

TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

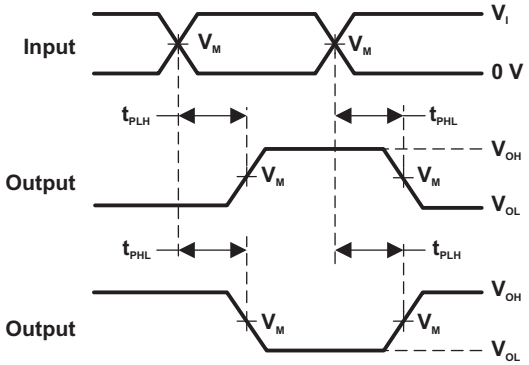
V_{CC}	INPUTS		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤2 ns	$V_{CC}/2$	2 × V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{CC}	≤2.5 ns	$V_{CC}/2$	2 × V_{CC}	50 pF	500 Ω	0.3 V



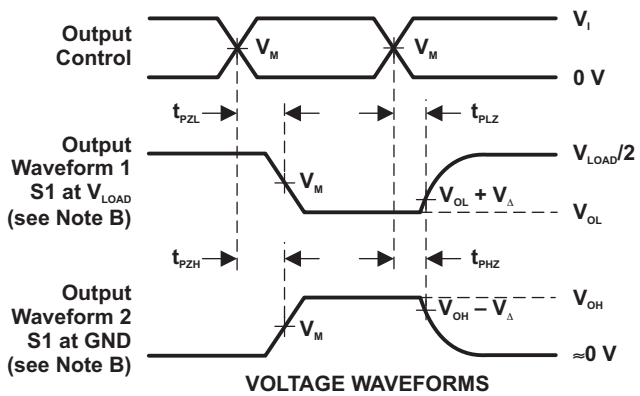
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω.
D. The outputs are measured one at a time, with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.
H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G32DCTR	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32 (R, Z)	Samples
SN74LVC2G32DCTRE4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32 (R, Z)	Samples
SN74LVC2G32DCTRG4	ACTIVE	SM8	DCT	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32 (R, Z)	Samples
SN74LVC2G32DCUR	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(C32Q, C32R) CR	Samples
SN74LVC2G32DCURE4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32R	Samples
SN74LVC2G32DCURG4	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32R	Samples
SN74LVC2G32DCUT	ACTIVE	VSSOP	DCU	8	250	Green (RoHS & no Sb/Br)	NIPDAU | SN	Level-1-260C-UNLIM	-40 to 125	(C32Q, C32R) CR	Samples
SN74LVC2G32QDCURQ1	ACTIVE	VSSOP	DCU	8	3000	Green (RoHS & no Sb/Br)	NIPDAU	Level-1-260C-UNLIM	-40 to 125	SUCQ	Samples
SN74LVC2G32YZPR	ACTIVE	DSBGA	YZP	8	3000	Green (RoHS & no Sb/Br)	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CGN	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

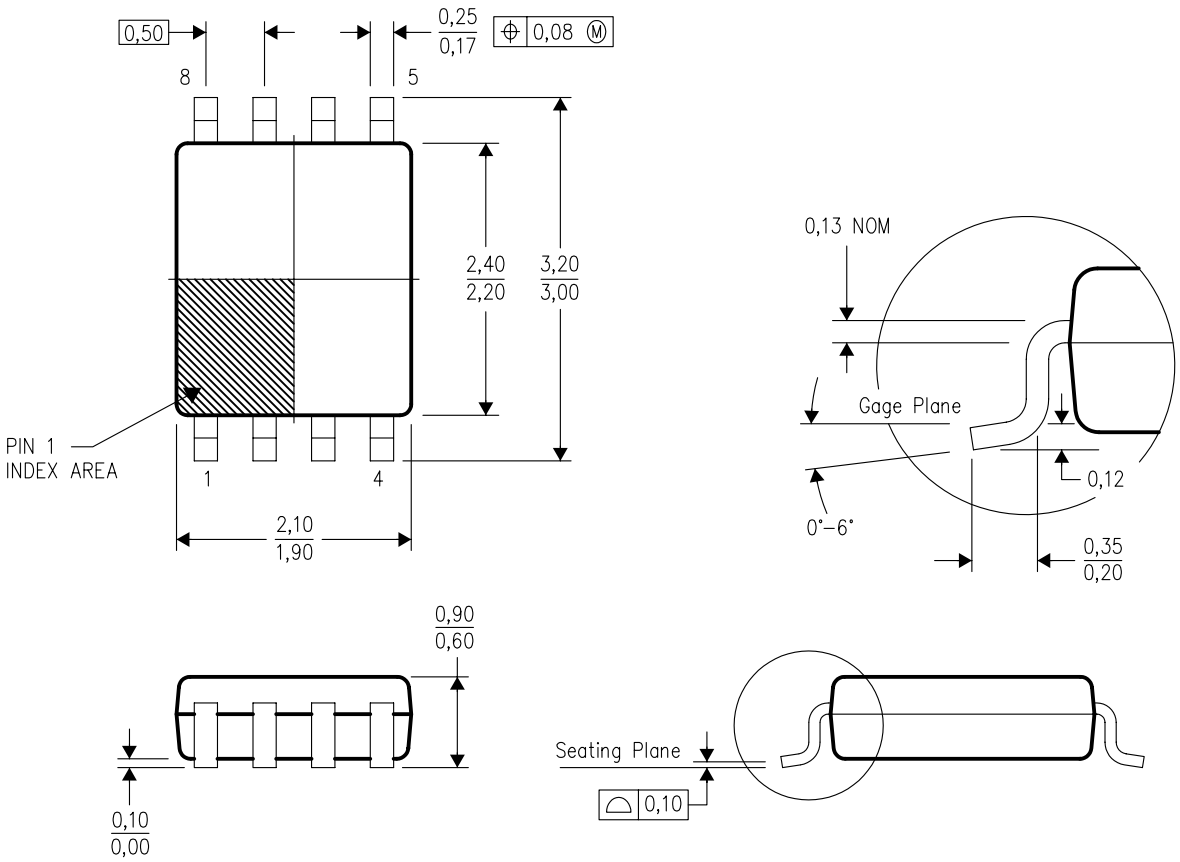
(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

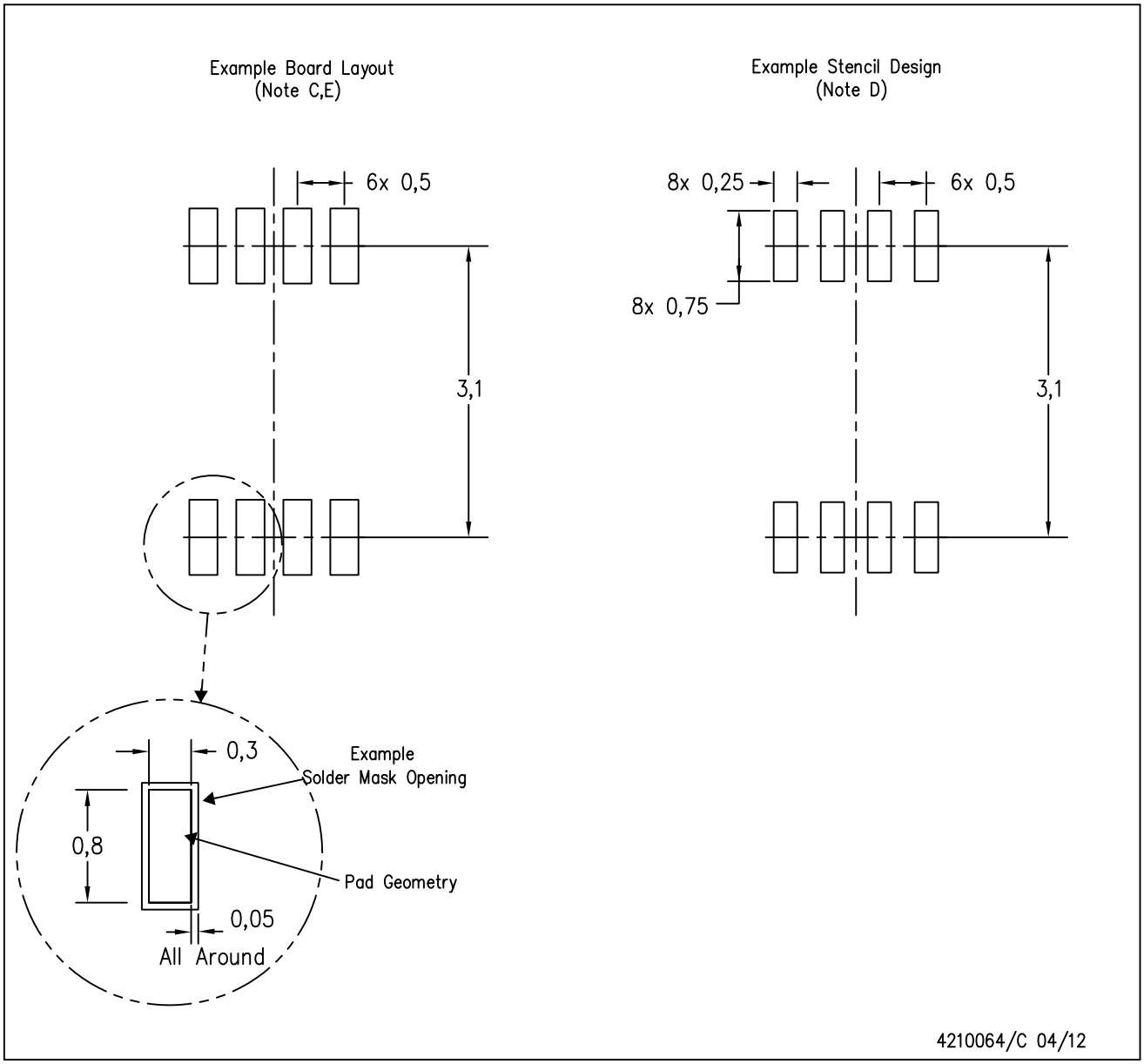
DCU (R–PDSO–G8) PLASTIC SMALL–OUTLINE PACKAGE (DIE DOWN)



4200503/F 07/05

NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO–187 variation CA.

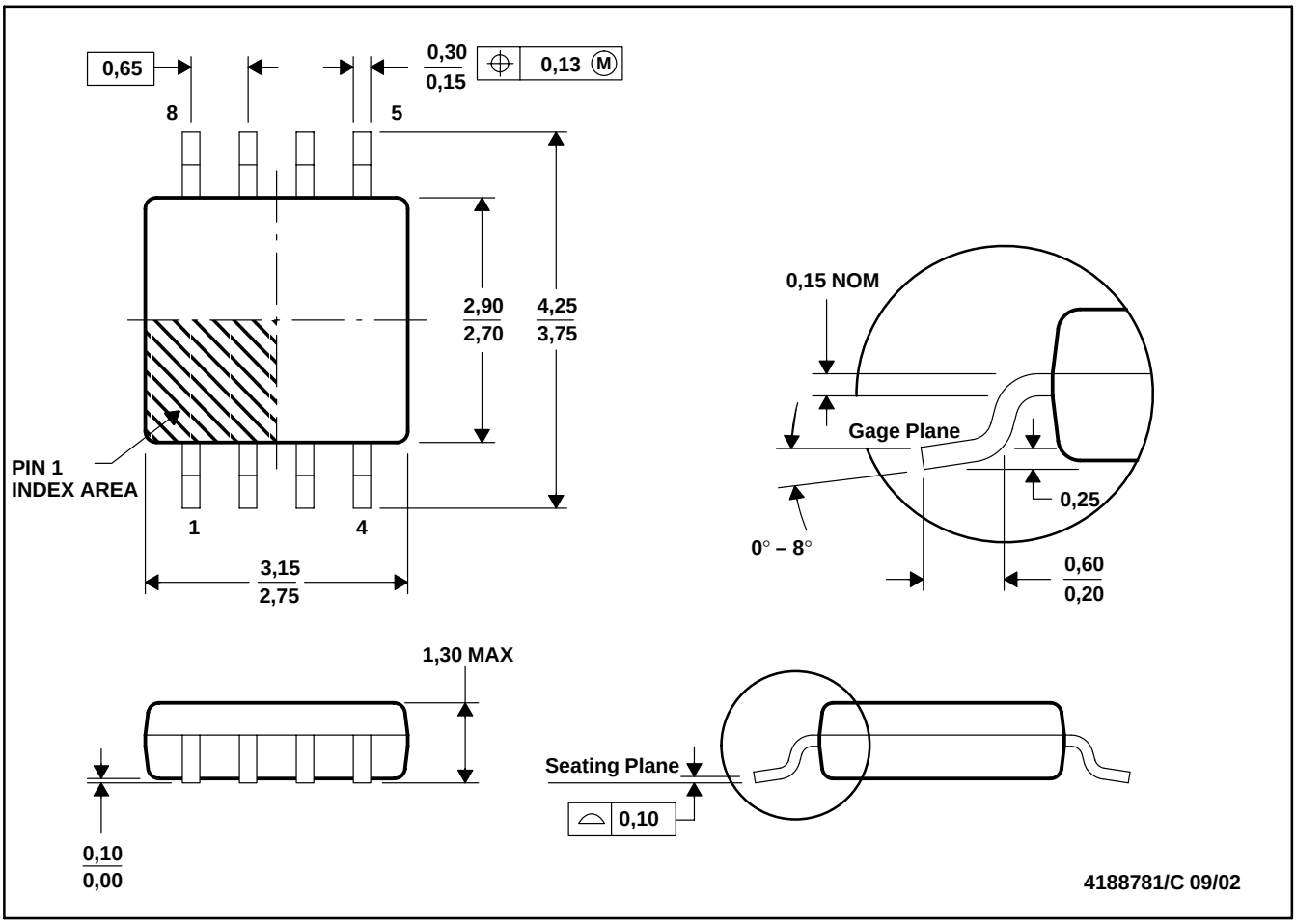
DCU (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

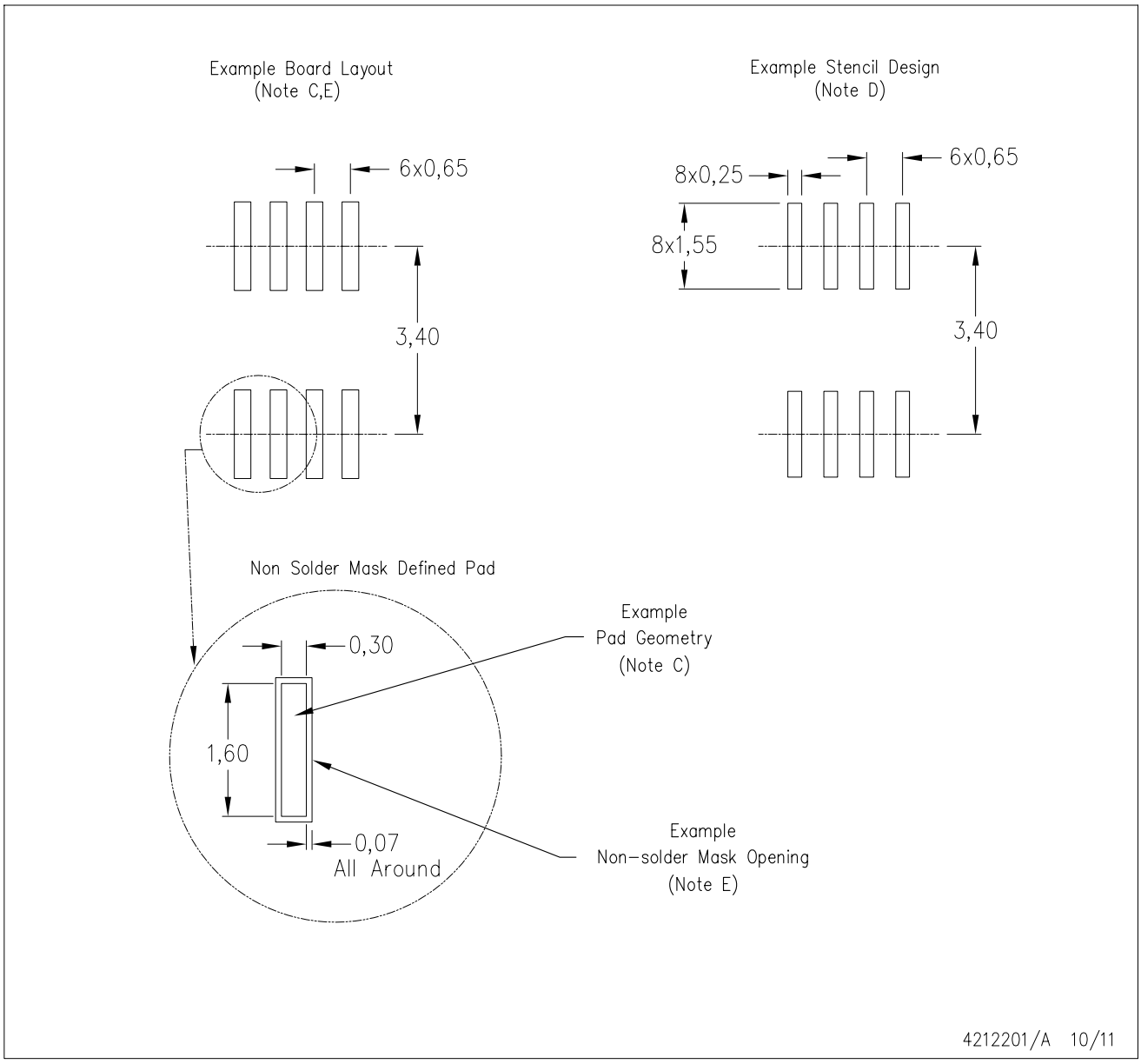
MPDS049B – MAY 1999 – REVISED OCTOBER 2002

DCT (R-PDSO-G8) **PLASTIC SMALL-OUTLINE PACKAGE**



NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion
D. Falls within JEDEC MO-187 variation DA.

DCT (R–PDSO–G8) PLASTIC SMALL OUTLINE



NOTES:
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B. This drawing is subject to change without notice.
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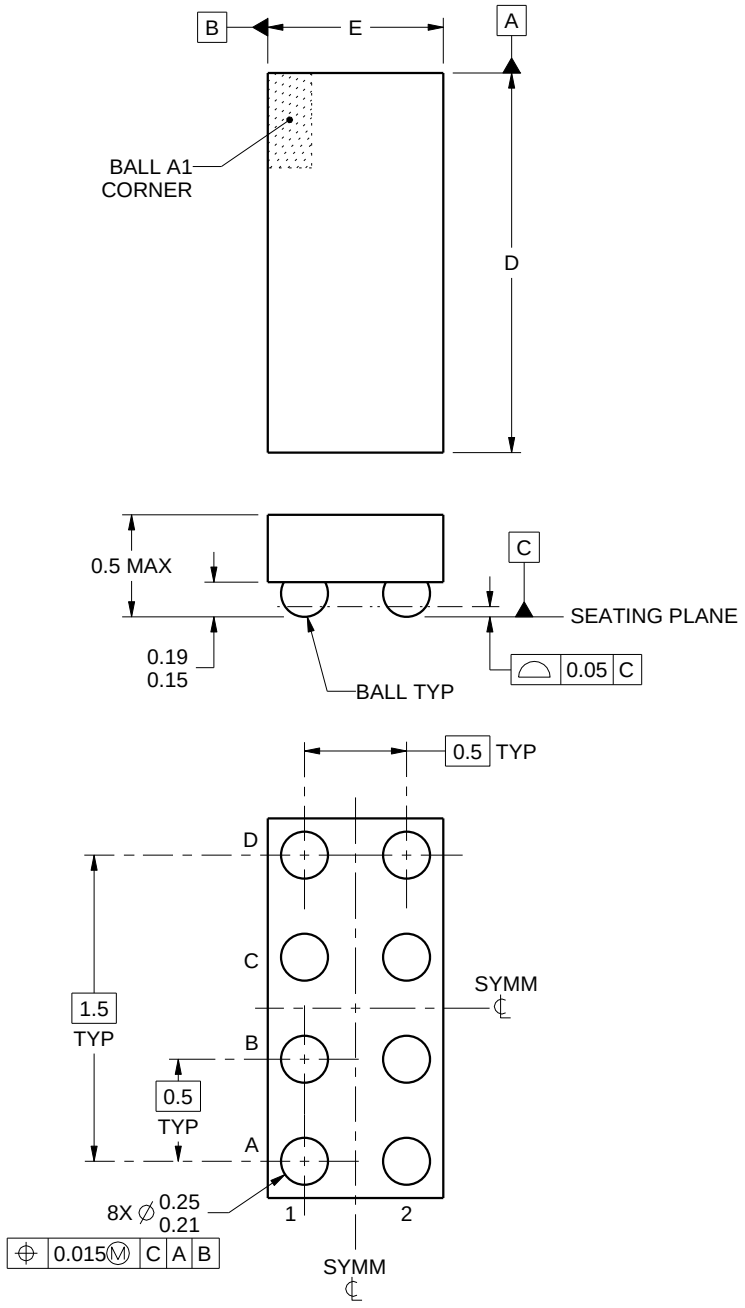
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PACKAGE OUTLINE

YZP0008

DSBGA - 0.5 mm max height

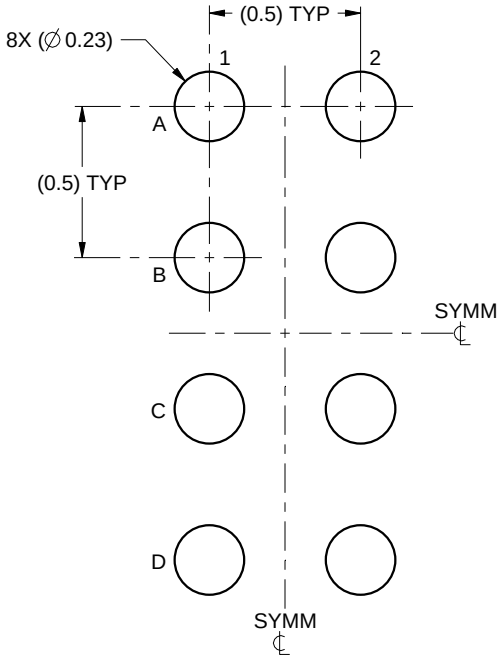
DIE SIZE BALL GRID ARRAY



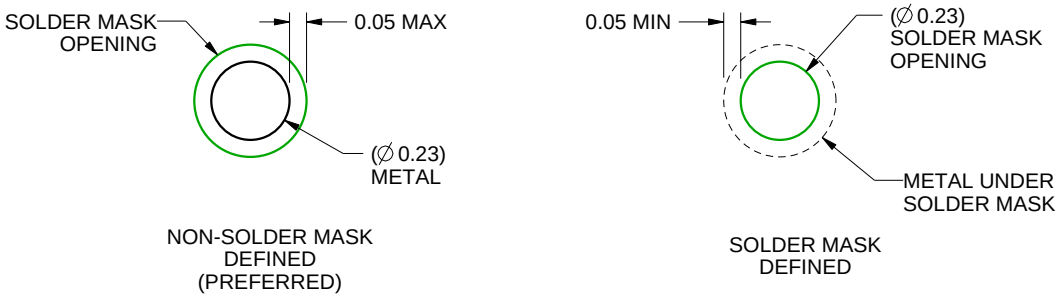
4223082/A 07/2016

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:40X

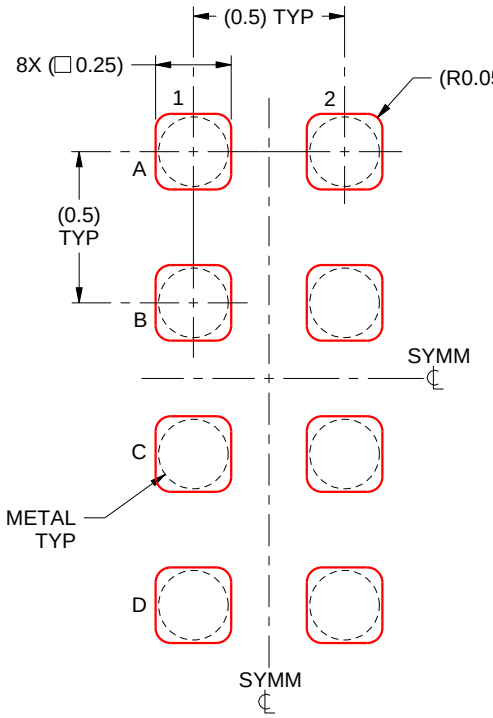


SOLDER MASK DETAILS
NOT TO SCALE

4223082/A 07/2016

NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:40X

4223082/A 07/2016

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

重要声明和免责声明

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